

Silicon PNP Power Transistors

2N6034 2N6035 2N6036

DESCRIPTION

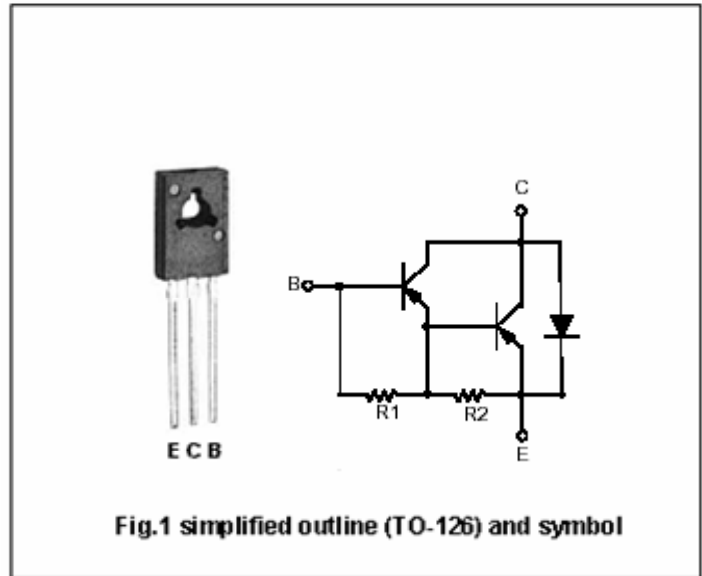
- With TO-126 package
- Complement to type 2N6037/6038/6039
- DARLINGTON
- High DC current gain

APPLICATIONS

- Designed for general-purpose amplifier and low-speed switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings(Ta= )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	2N6034	-40	V
		2N6035	-60	
		2N6036	-80	
V <sub>CEO</sub>	Collector-emitter voltage	2N6034	-40	V
		2N6035	-60	
		2N6036	-80	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-4	A
I <sub>CM</sub>	Collector current-peak		-8	A
I <sub>B</sub>	Base current		-0.1	A
P <sub>D</sub>	Total Power Dissipation	T <sub>C</sub> =25	40	W
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th j-c</sub>	Thermal resistance junction to case	3.12	/W

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE0(SUS)</sub>	Collector-emitter sustaining voltage	2N6034	-40			V
		2N6035	-60			
		2N6036	-80			
V <sub>CEsat-1</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-2A; I <sub>B</sub> =-8mA			-2.0	V
V <sub>CEsat-2</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-4A; I <sub>B</sub> =-40mA			-3.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-4A; I <sub>B</sub> =-40mA			-4.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-2A; V <sub>CE</sub> =-3V			-2.8	V
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =Rated V <sub>CE0</sub> ; I <sub>B</sub> =0			-0.1	mA
I <sub>CEx</sub>	Collector cut-off current	V <sub>CE</sub> =Rated V <sub>CE0</sub> ; V <sub>BE(off)</sub> =1.5V T <sub>C</sub> =125			-0.1 -0.5	mA
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =Rated V <sub>CBO</sub> ; I <sub>E</sub> =0			-0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-2.0	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-0.5A; V <sub>CE</sub> =-3V	500			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-2A; V <sub>CE</sub> =-3V	750		15000	
h <sub>FE-3</sub>	DC current gain	I <sub>C</sub> =-4A; V <sub>CE</sub> =-3V	100			
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =-10V; f=0.1MHz			200	pF

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PACKAGE OUTLINE

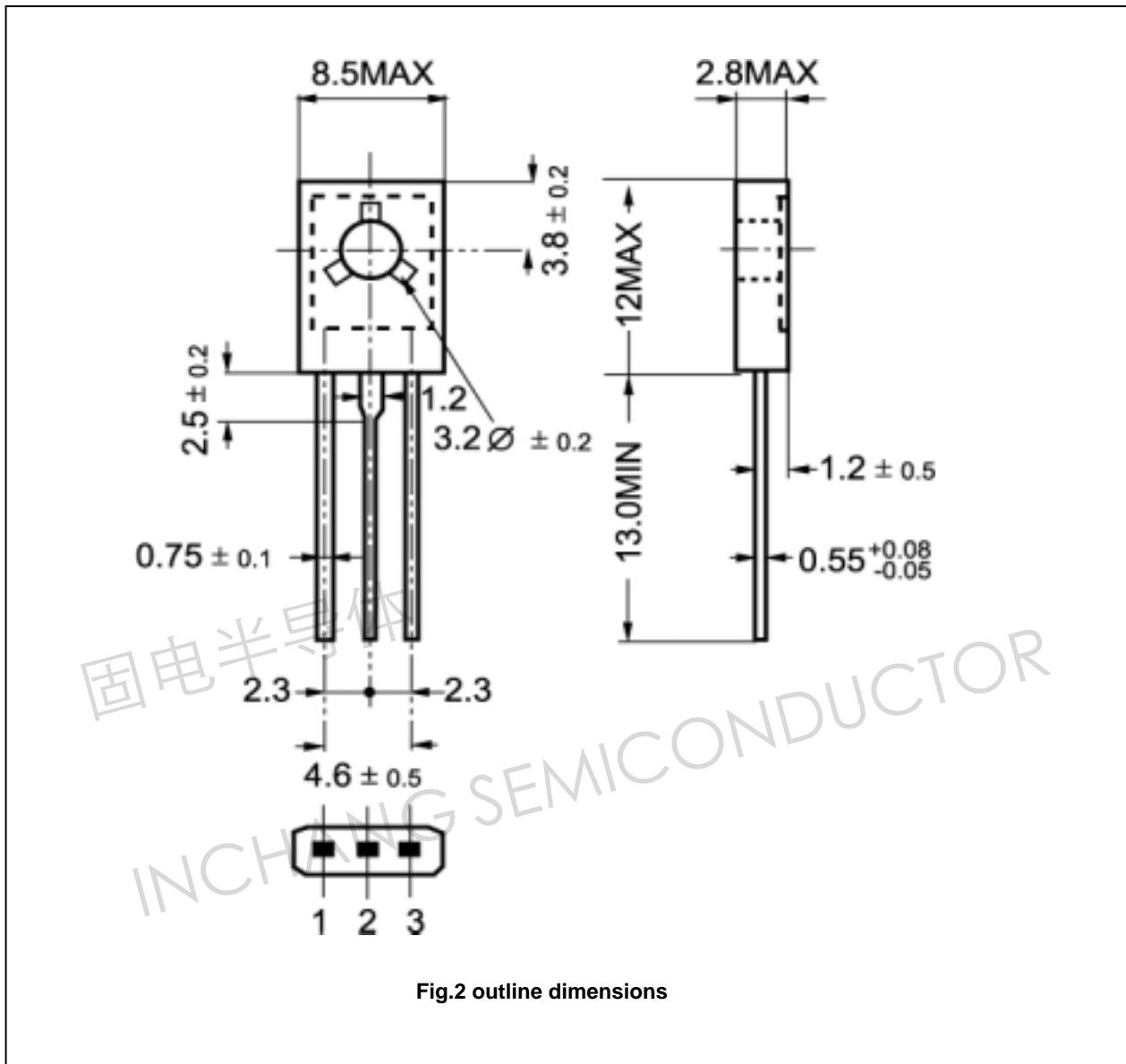


Fig.2 outline dimensions